1. Scope

The present specifications shall apply to an SJPE-H4.

2. Outline

| | |
|---|---|
| Type | Silicon Schottky Barrier Diode |
| Structure | Resin Molded |
| Applications | High Frequency Rectification |

3. Flammability

UL94V-0(Equivalent)

4. Absolute maximum ratings

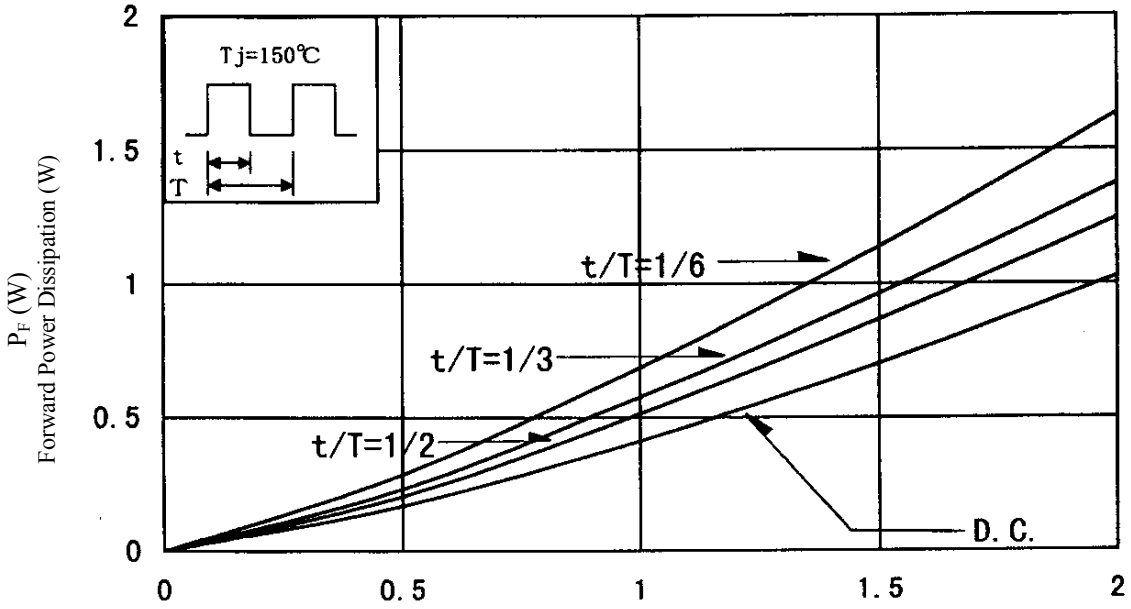
| No. | Item | Symbol | Unit | Rating | Conditions |
|---|---|---|---|---|---|
| 1 | Transient Peak Reverse Voltage | $V_{RSM}$ | V | 40 | — |
| 2 | Peak Reverse Voltage | $V_{RM}$ | V | 40 | — |
| 3 | Average Forward Current | $I_{F(AV)}$ | A | 2.0 | Refer to Derating of 7 |
| 4 | Peak Surge Forward Current | $I_{FSM}$ | A | 40 | Half sinewave, one shot |
| 5 | $I^2t$ Limiting Value | $I^2t$ | $A^2s$ | 8.0 | 1msec≤ t≤ 10msec |
| 6 | Junction Temperature | $T_j$ | °C | -40~+150 | — |
| 7 | Storage Temperature | $T_{stg}$ | °C | -40~+150 | — |

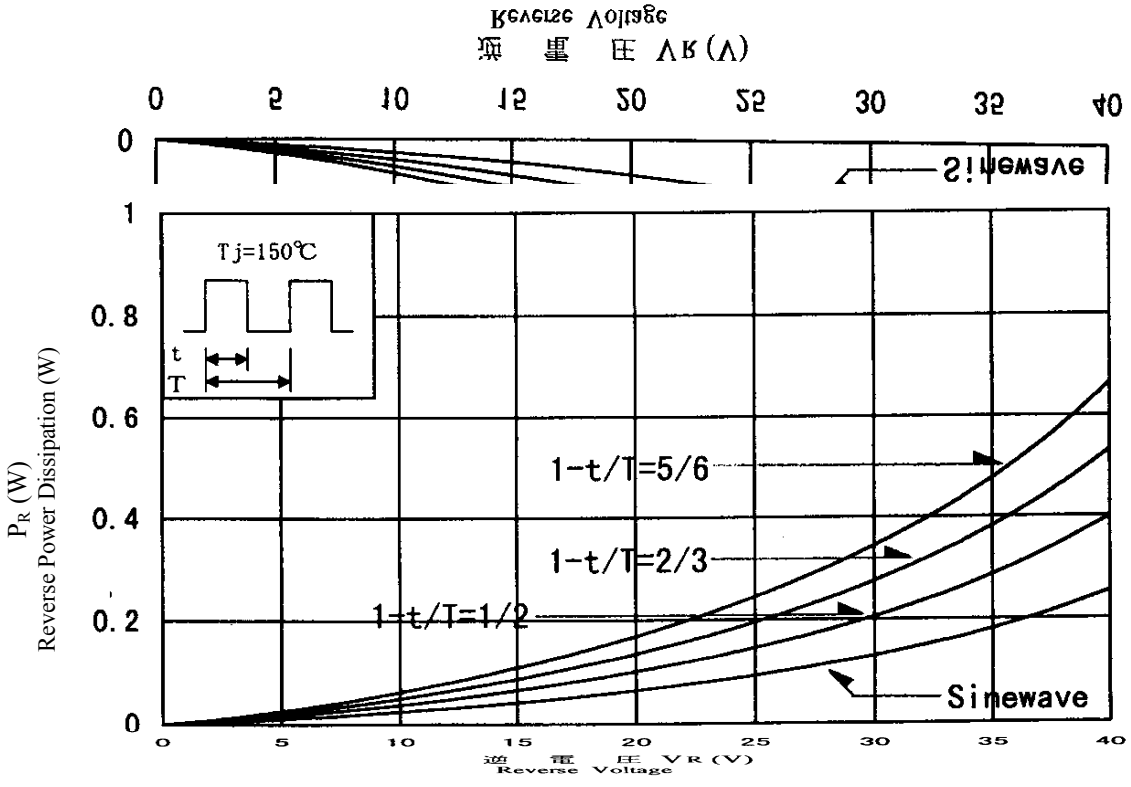
5. Electrical characteristics (Ta=25°C,unless otherwise specified)

| No. | Item | Symbol | Unit | Value | Conditions |
|---|---|---|---|---|---|
| 1 | Forward Voltage Drop | $V_F$ | V | 0.6 max. | $I_F$=2.0A |
| 2 | Reverse Leakage Current | $I_R$ | μA | 50 max. | $V_R=V_{RM}$ |
| 3 | Reverse Leakage Current Under High Temperature | H・$I_R$ | mA | 20 max. | $V_R=V_{RM}$, $T_j$=150°C |
| 4 | Thermal Resistance | $R_{th(j-l)}$ | °C /W | 20 max. | Between Junction and lead |

6. Characteristics

$I_{F(AV)}$ - $P_F$

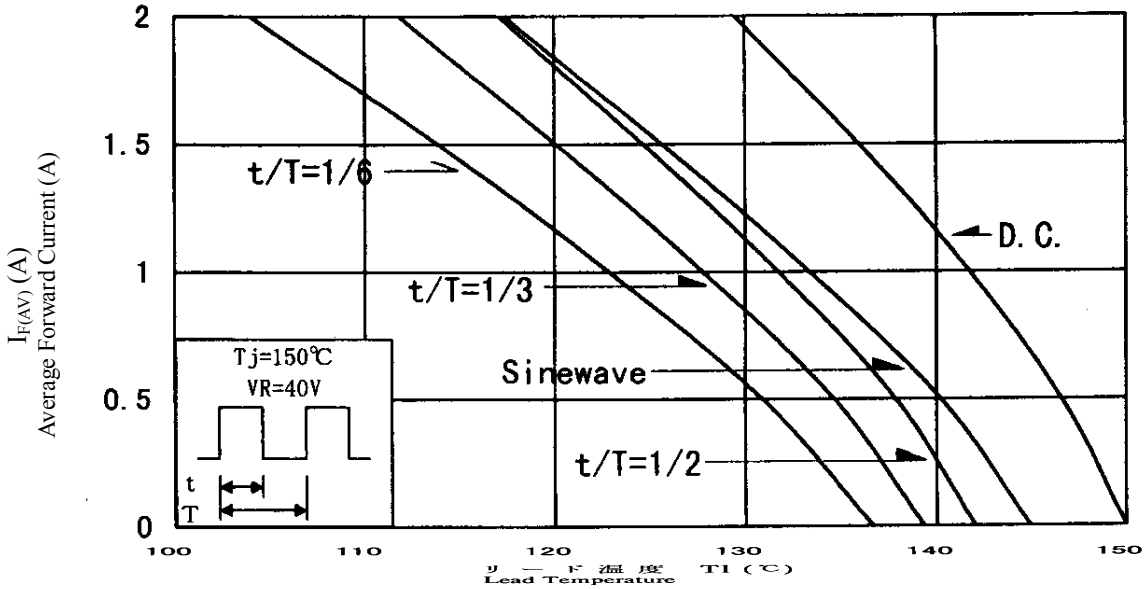



$V_R$ (V)
Reverse Voltage (V)

7. Derating

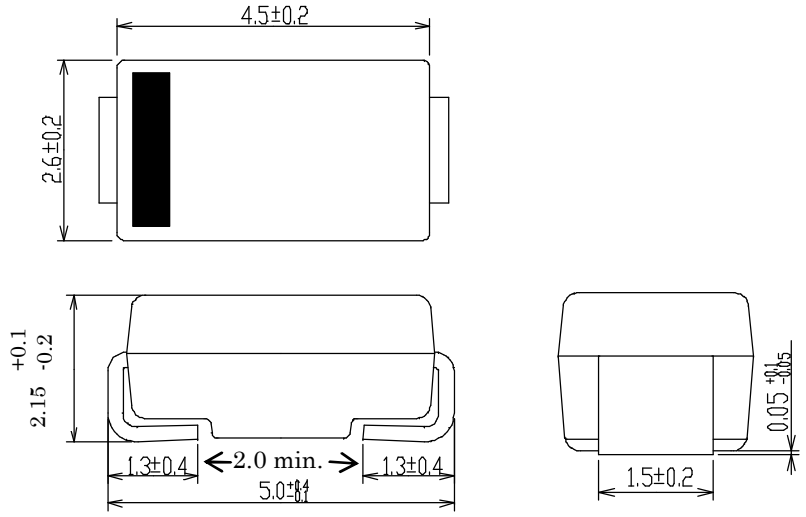
$T_l$ - $I_{F(AV)}$ $V_R$=40(V)




$T_l$ (°C)
Lead Temperature (°C)

8. Package information

8-1Package type, physical dimensions and material

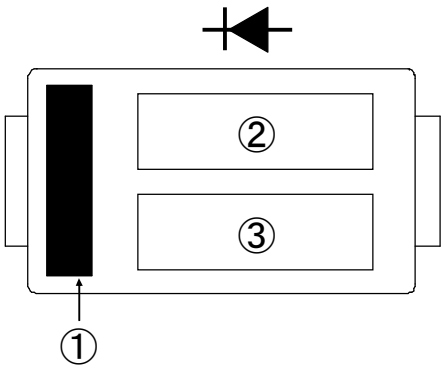



単位：㎜
Dimensions in ㎜

8-2Appearance

The body shall be clean and shall not bear any stain, rust or flaw.

8-3Marking




① Polarity marking (Cathode band)

② Type number
SJPE-H4 as abbreviated of EH4

③ Lot number
Example) 6718
6:Last number of Year
7: Month from 1 to 9 for Jan. to Sep.
O for Oct., N for Nov., D for Dec.
18: Day